

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION Generic Copy

02-JUN-2004

SUBJECT: ON Semiconductor Final Product/Process Change Notification 13495

TITLE: Final Notification for Transfer of Mosaic 1 & 1.5 Devices to ONCR/Tesla Fab

EFFECTIVE DATE: 02-Aug-2004

AFFECTED CHANGE CATEGORY:

- ON Semiconductor Fab Site
- Wafer Process

AFFECTED PRODUCT DIVISION:

- Analog Products Div
- Logic Products

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Representative or Don Warring <RRGA60@onsemi.com>

SAMPLES: Contact Below

Contact your local ON Semiconductor Sales Representative or Josh Warner <R47830@onsemi.com>

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact Sales Representative or Gregg Hooker <FFMGNR@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 60 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

This is the Final PCN to notify customers that the changes described in Initial PCN# 12671, located at www.onsemi.com, have been completed for the MC100ELT21, MC10H161, MC10H135, MC100H602, MC10H159, MC10H105, MC10H103, and the MC10H100 product families.

ON Semiconductor is pleased to announce the continuation of the MOSAIC 1.0/1.5 FAB transfer process to our internal factory ON Semiconductor Czech Republic (ONCR; Formerly Tesla), located in Roznov, Czech Republic, to manufacture MOSAIC 1.0/1.5 Bipolar Technology products. The ONCR Fab is an ISO9001 certified facility and currently manufactures the Analog product family. MOSAIC 1.0/1.5 products were previously fabricated in the Motorola Bipolar Manufacturing Center (BMC) in Mesa, Arizona.



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This is the Final PCN only for the MC100ELT21, MC10H161, MC10H135, MC100H602, MC10H159, MC10H105, MC10H103, and the MC10H100 product families. Additional notifications will be issued separately for subsequent products when they have completed all qualification testing.

Device parameters will continue to meet all Data Book specifications, and reliability will continue to meet or exceed ON Semiconductor standards.

In the course of reviewing the electrical data for the parts released, test methodology improvements indicate prior limits for linh were imprecisely set. A more accurate set of Minimum and Maximum limits will be corrected on the next revision of the datasheet to reflect these changes. Changes to released parts include the MC100ELT21, and the MC100H602, where changes are listed below.

Old MC100ELT21 Limits: IINH Limits for PECL DC temperature ranges: Change -40 degrees C was 150 uA and will be changed to 255 uA Change 25, 85 degrees C was 150 uA and will be changed to 175 uA

Old MC100H602 Limits: IINH Limits for 10H and 100H ECL DC temperature ranges: Change IIH to IINH, but don't change the name of TTL DC IIH Change 0 degrees C from 225 uA to 255 uA Change 25 & 85 degrees C from 145 uA to 175 uA Change TPHL Limits for 100H602 AC Characteristics for MR: OLD 0 degrees C was 2.0 nS min and 3.4 nS max NEW 0 degrees C is 2.7 nS min and 4.1 nS max OLD 25 degrees C was 2.1 nS min and 3.5 nS max NEW 25 degrees C is 2.8 nS min and 4.2 nS max OLD 85 degrees C was 2.5 nS min and 3.9 nS max NEW 85 degrees C is 3.2 nS min and 4.6 nS max

There were no changes to the actual design or function of the parts.

RELIABILITY DATA SUMMARY:

Below is a summary of the reliability results. A more detailed reliability report is available upon request.

Test High Temp Op Life (HTOL)	Conditions Tj =150DegC for 2016 hours Tj =150DegC for 504 hours	Results 0/394 0/79
High Temp Bake (HTB)	175DegC for 504 hours 150DegC for 1008 hours	0/320 0/80
Preconditioning for MSL-1 (PC)	IR at 260DegC, TC, HAST, AC IR at 220DegC, TC, HAST, AC	0/718 0/320
PC-HAST	130DegC/85% RH/18.8 PSIG for 96 hours	0/315
PC Autoclave (AC)	121DegC/100% RH/15 PSIG for 96 hours	0/320
PC-Temp Cycling (TC)	-65DegC to +150DegC; for 500 cycles	0/400



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Test PC-Temp Cycling w/PC	Conditions -65DegC to +150DegC; for 500 cycles	Results 0/80
Bond Pull Strength (BPS)	Per Factory Testing with CpK>= 1.33	PASS
Bond Shear Test (BS)	Per Factory Testing with CpK>= 1.33	PASS
ESD per JEDEC Standard	Human Body Model (HBM) Machine Model (MM) Charge Device Model (CDM)	MEETS CRITERIA
Destructive Physical Analysis (DPA)	Analysis done after PC-Temp Cycling	PASS
Construction Analysis (CA)	Compare to BMC results	MEETS OR EXCEEDS CRITERIA

Qualification Vehicle Justification Technology Qualification Dev

Technology	Qualification Device	Reason Chosen
MOSAIC1/1.5	MC10H605FN	Large Die, Highest Voltage,
		Schottky Diodes
	MC10H141FN	Complexity
	MC10H125P	Translator Function
	MC10ELT21D	Translator Function

Reliability Test Conclusions:

Reliability test data is consistent with passing ON Semiconductor requirements.

ELECTRICAL CHARACTERISTIC SUMMARY

Characterization data is available upon request.

CHANGED PART IDENTIFICATION

Product after work week 22 2004 will be from the ONCR fab.

AFFECTED DEVICE LIST (WITHOUT SPECIALS):

PART MC100ELT21D MC100ELT21DR2 MC100ELT21DR2G MC100ELT21DT MC100ELT21DTR2 MC100H602FN MC10H100L MC10H100M MC10H100M MC10H100M MC10H103FN MC10H103FNR2 MC10H103L



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MC10H103M MC10H103MEL MC10H103P MC10H103PG MC10H105FN MC10H105FNR2 MC10H105L MC10H105M MC10H105MEL MC10H105P MC10H105PG MC10H135FN MC10H135FNR2 MC10H135L MC10H135M MC10H135P MC10H135PG MC10H159FN MC10H159FNR2 MC10H159L MC10H159M MC10H159MEL MC10H159P MC10H159PG MC10H161FN MC10H161FNR2 MC10H161L MC10H161M MC10H161MEL MC10H161P MC10H161PG